



中国科学技术大学

University of Science and Technology of China

STCF

# Injector and positron source of STCF in China

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**15th November**

**Workshop on future Super c-tau factories 2021**



**I. The injector of STCF**

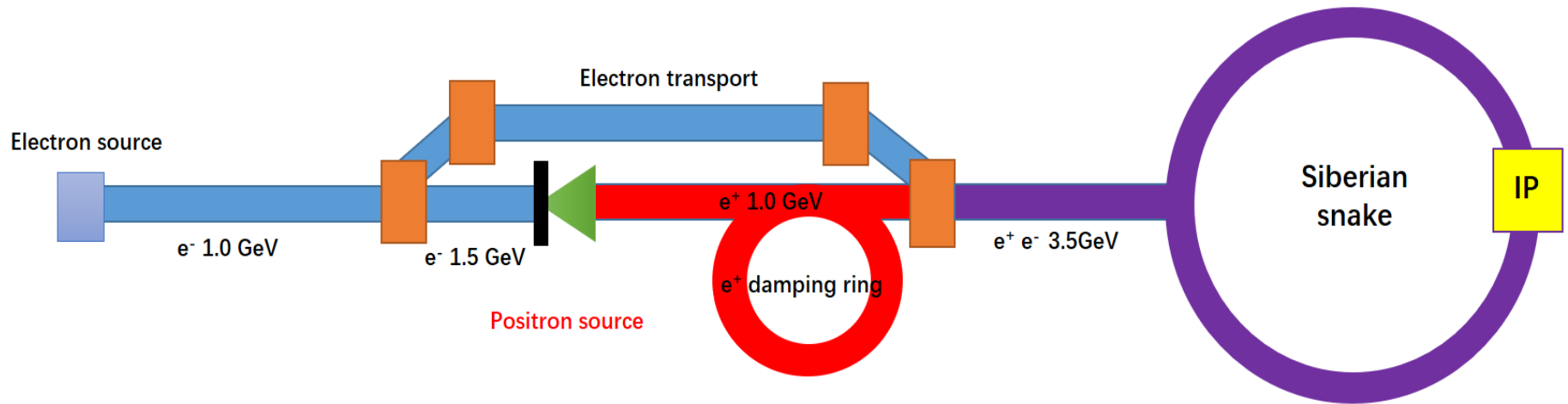
**II. The thermal research of single-crystal  
tungsten target**

**III. The new target design for positron**



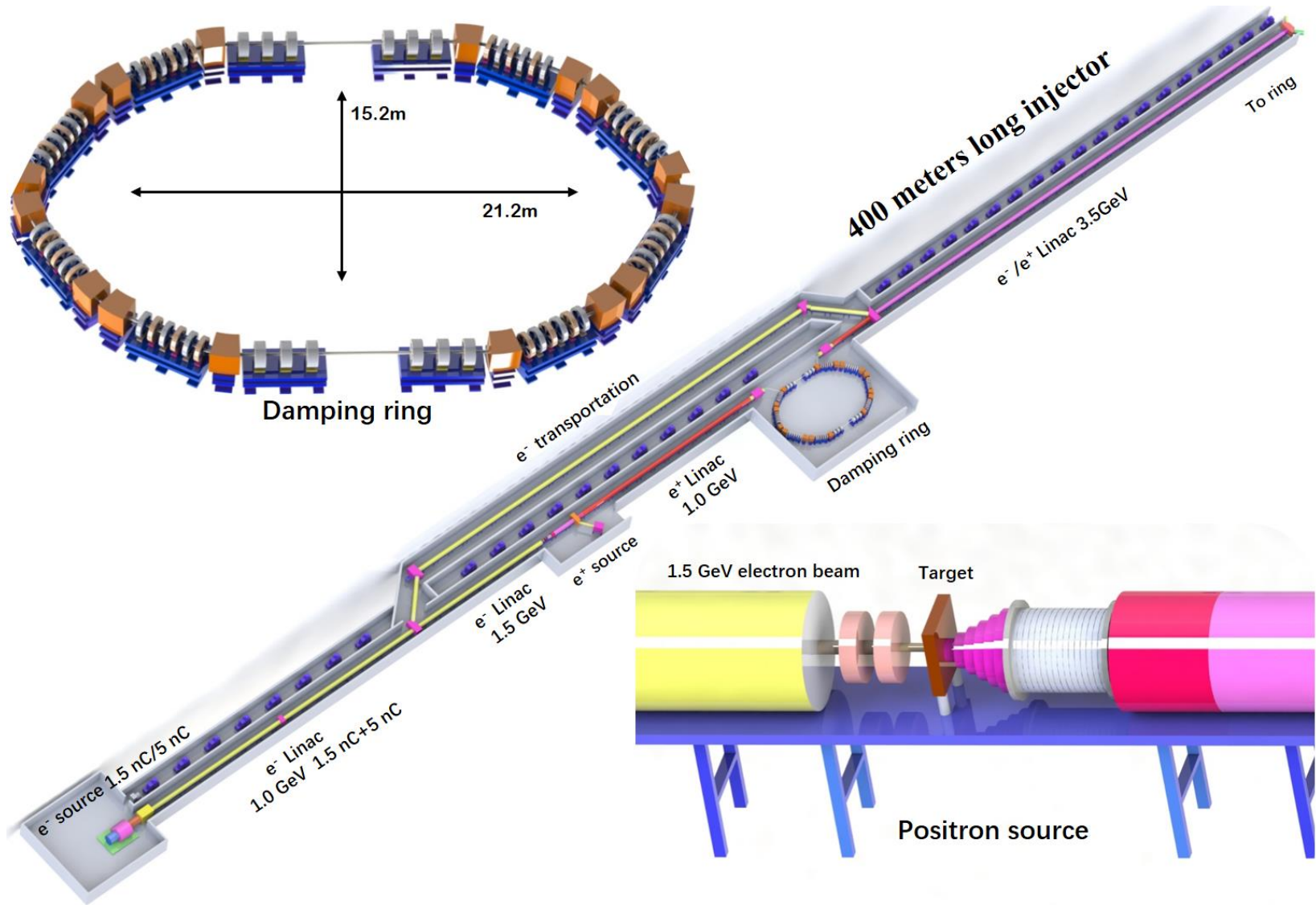
# The Super Tau-Charm Facility in China

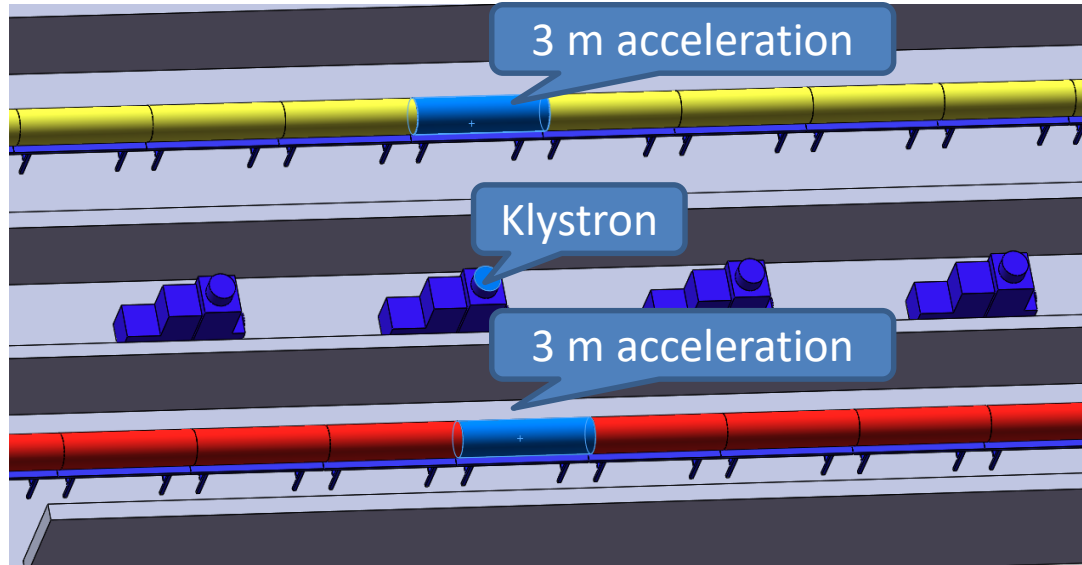
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Parameter	Value
Perimeter/m	600~800
Optimized beam energy/GeV	2
Energy/GeV	1-3.5
Current/A	1.5
Emittance( $\epsilon_x/\epsilon_y$ )/nm·rad	5/0.05
$\beta(\beta_x^*/\beta_y^*)$ /mm	90/0.9
Crossing Angle $2\theta$ /mrad	60
Frequency shift $\xi$	0.06
Hourglass	0.8
Luminosity/ $\times 10^{35} \text{cm}^{-2} \text{s}^{-1}$	$\geq 0.5$

# The injector of STCF

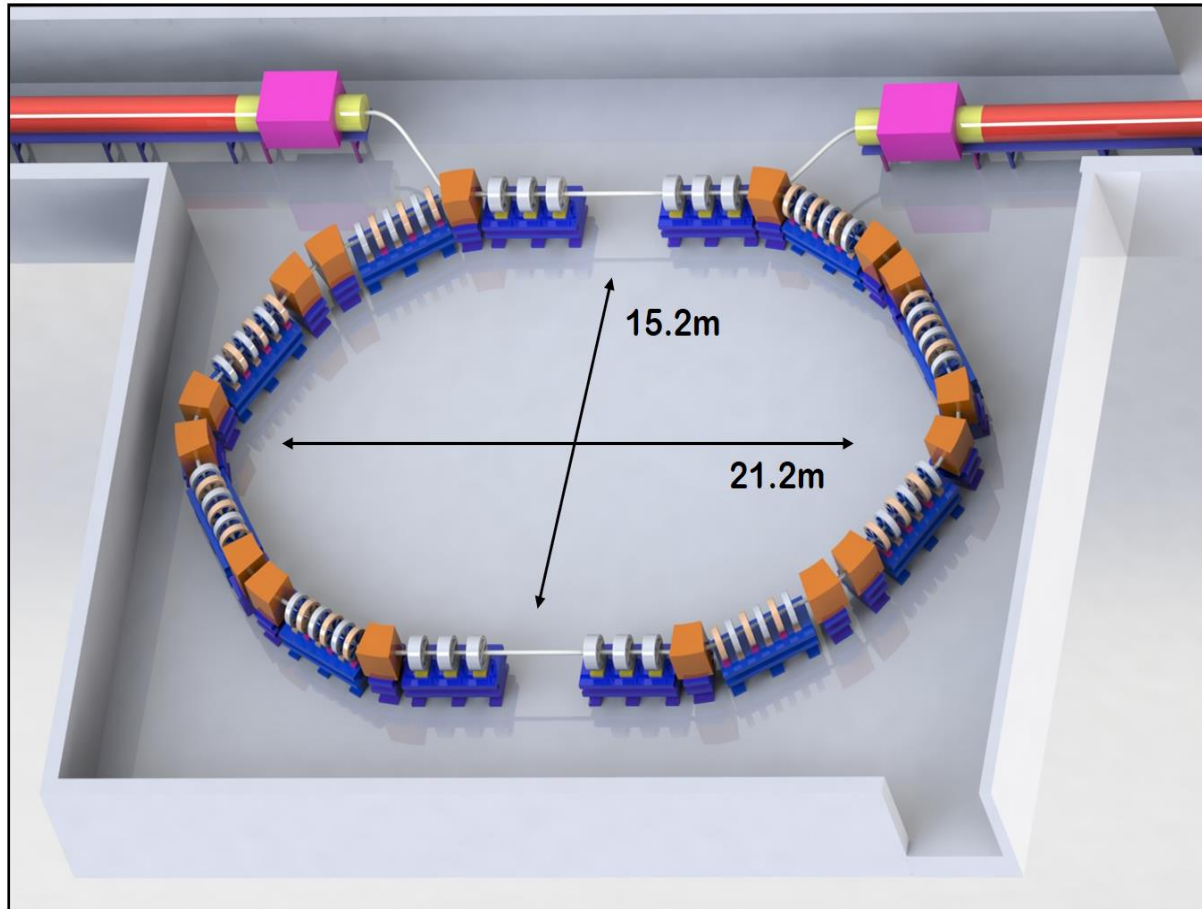




Parameter	Value
Klystron	1
Frequency, $f_0$	2856 MHz
Repetition frequency	0-50 Hz
Peak power	50 MW
Pulse width	3.5 $\mu$ s
SLED	1
Amplification factor	5
output power	250 MW
Number of acceleration	2
Accelerating gradient	23MeV/m
Energy gain	134MeV

# Damping ring

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Parameter	Value
Energy	1.0 GeV
Perimeter	~58 mm
Repetition frequency	50 Hz
Bending radius	2.7 m
Dipole magnets, $B_0$	1.4 T
Momentum compression factor, $\alpha_c$	0.076
$U_0$	35.8 keV
Damping time x/y/z	12/12/6 ms
$\delta_0$	0.05%
$\epsilon_0$	287.4 mm·mrad
Bunch length	7 mm
$\epsilon_{inj}$	2500 mm·mrad
$\epsilon_{ext\ x/y}$	704/471 mm·mrad
$\delta_{inj}/\delta_{ext}$	0.3/0.06
Divergence of energy	1%
$f_{rf}$	650 MHz
$V_{rf}$	1.8 Mv



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# Thermal conductivity of single crystal tungsten

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The thermal conduction can be presented as

$$k = \frac{J}{\partial T / \partial x}$$

The empirical N-body potential was used for tungsten by Finnis and Sinclair. In the F-S potential, the total potential energy of system is expressed as

$$E = E_p + E_N$$

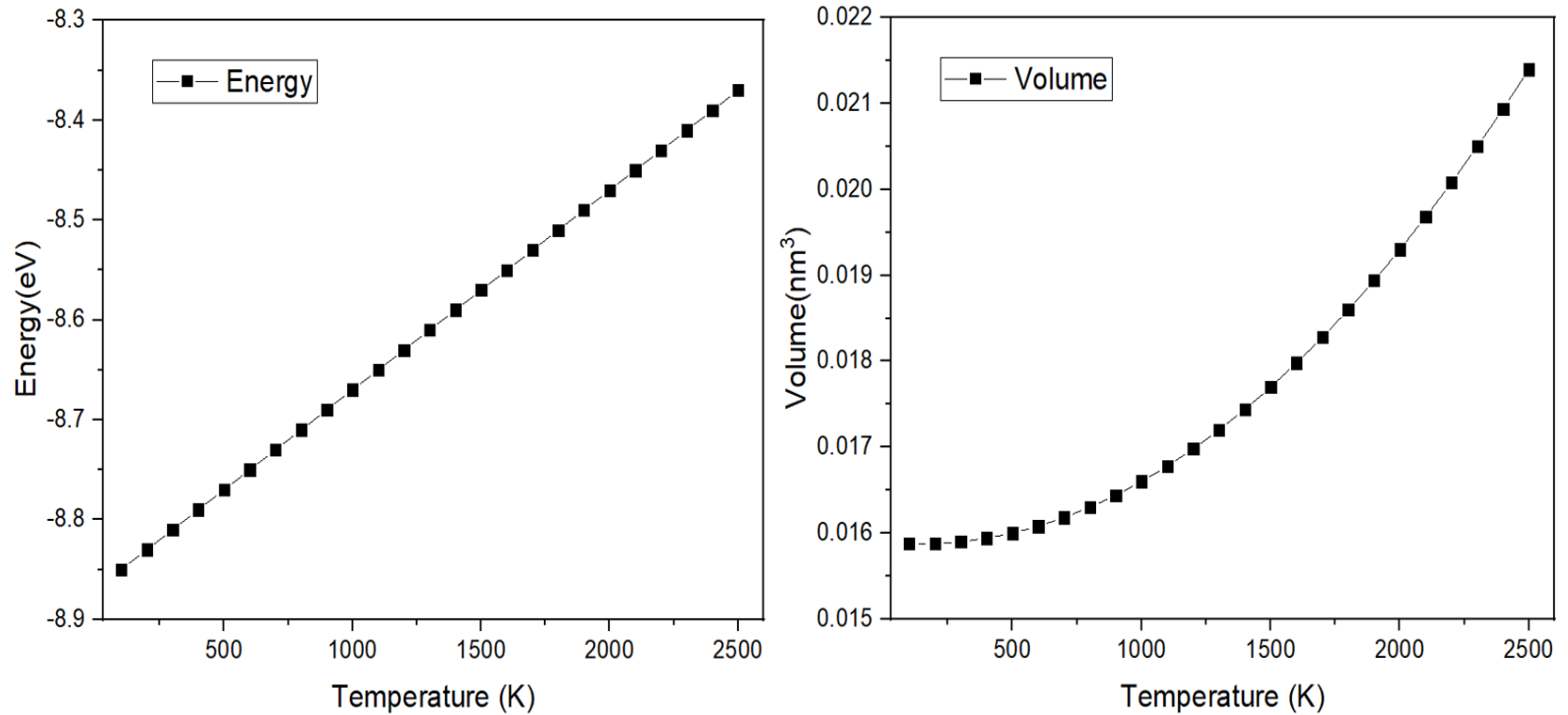
$$\varphi(r_{ij}) = \begin{cases} B & r_{ij} \leq r_{c1} \\ B_0 + B_1 r_{ij} + B_2 r_{ij}^2 & r_{c1} < r_{ij} < r_{c2} \\ (r_{ij} - d)^2 & r_{c2} \leq r_{ij} < d \\ 0 & r_{ij} \geq d \end{cases}$$



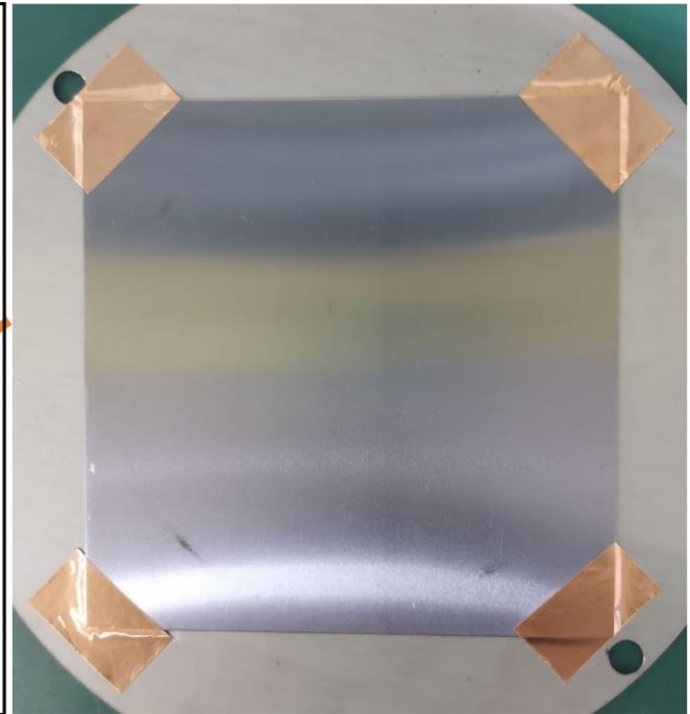
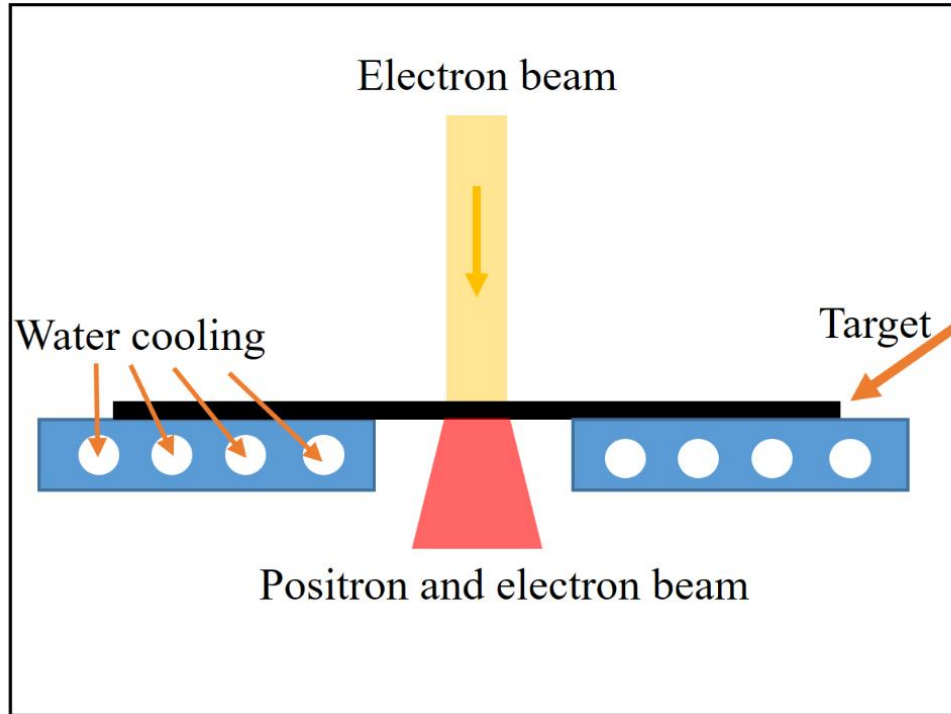


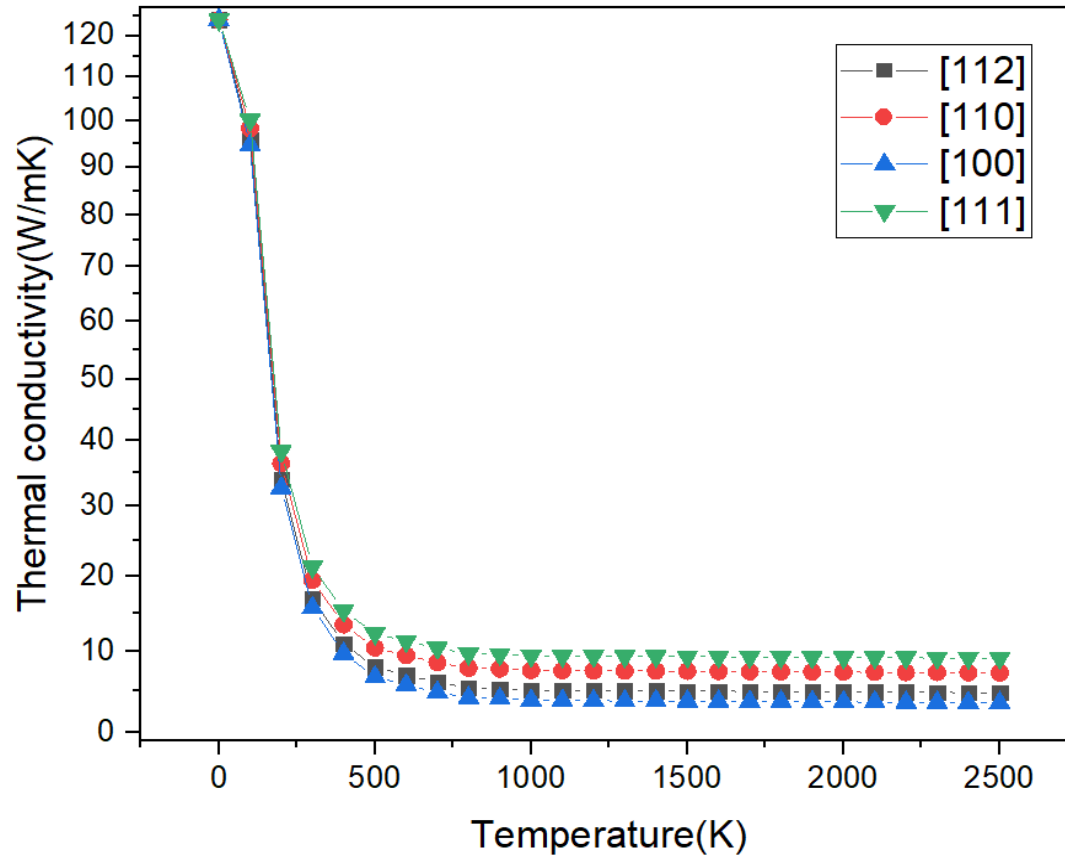
# Positron source for STCF

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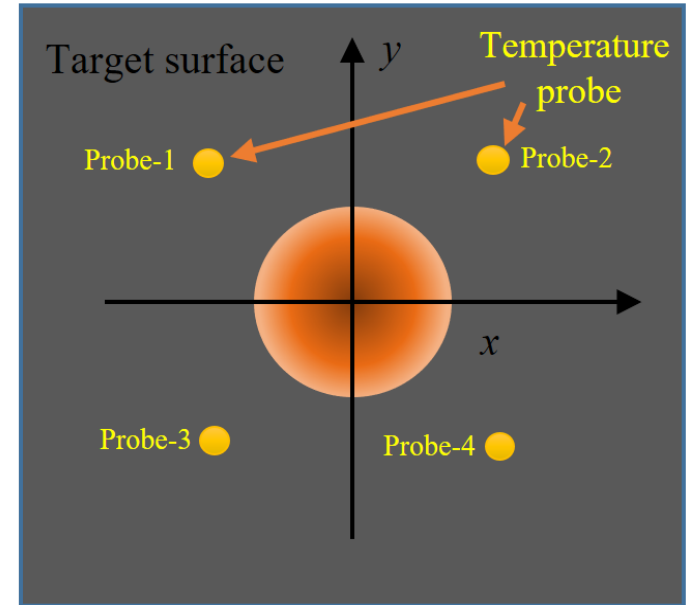
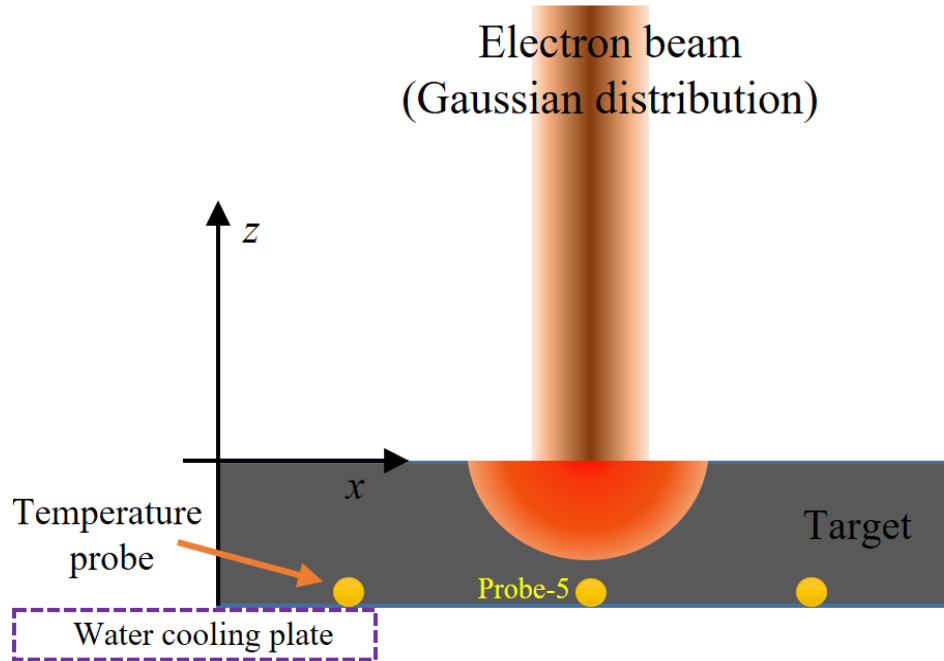


The time averaged total energy of one tungsten atom (left) and the time averaged volume (right) as functions of temperature.

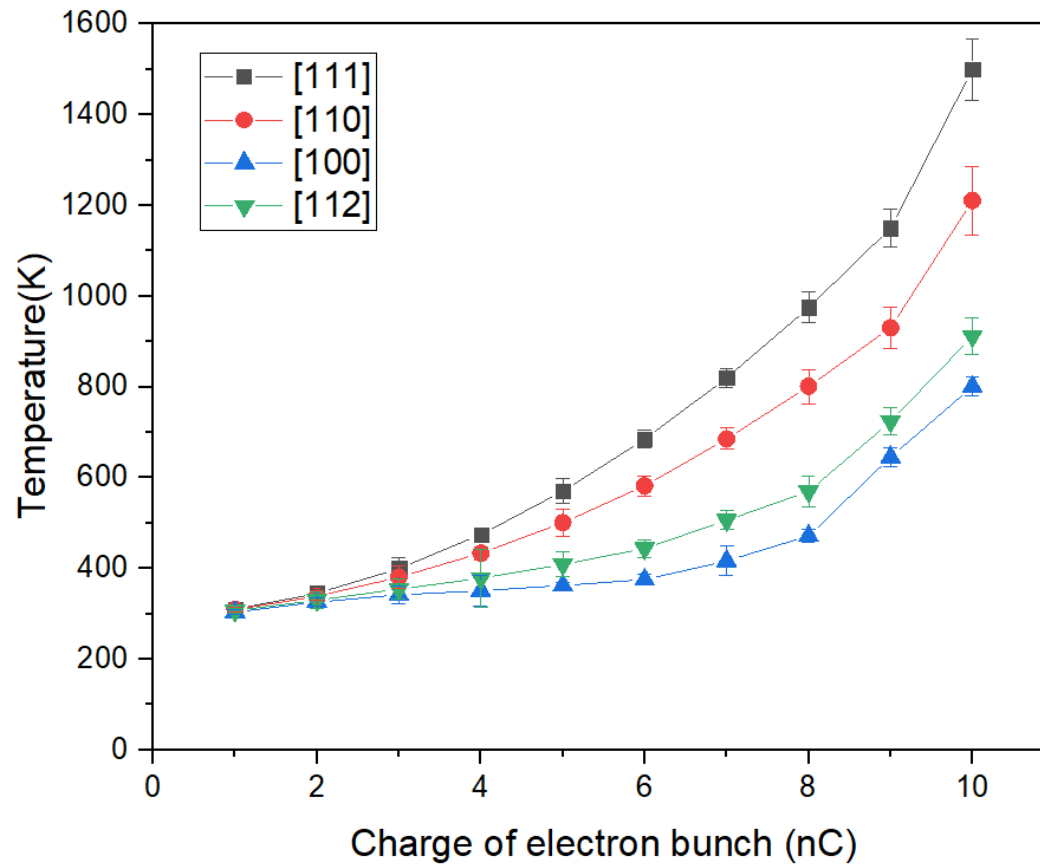




Simulation results of the thermal conductivity for different crystallographic orientation of various temperatures



The experiment diagram of thermal conductivity measurement

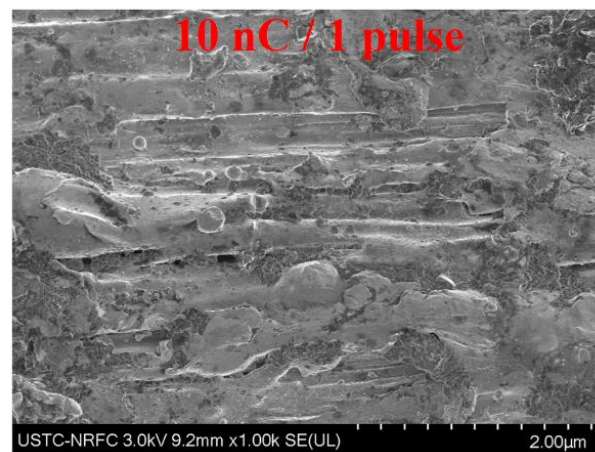
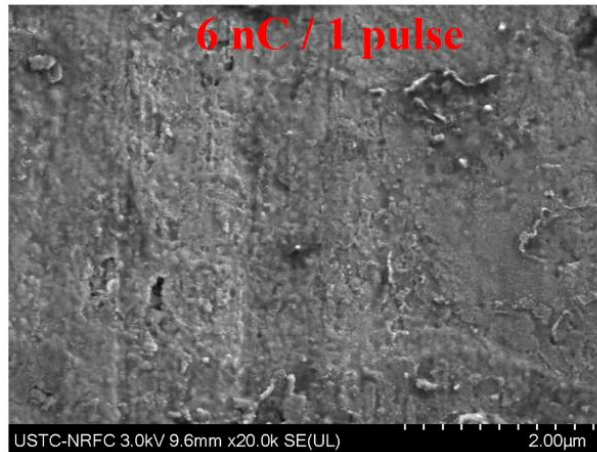
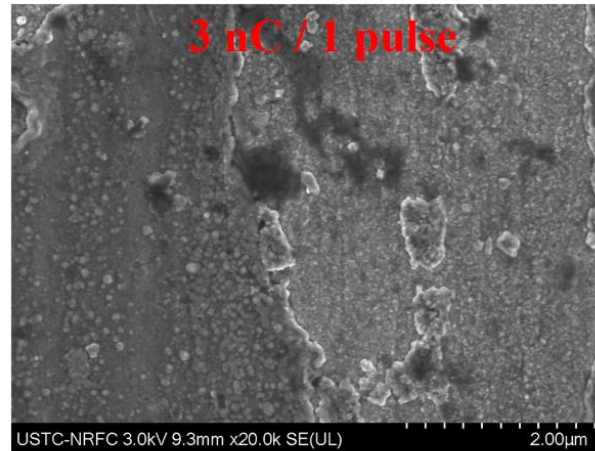
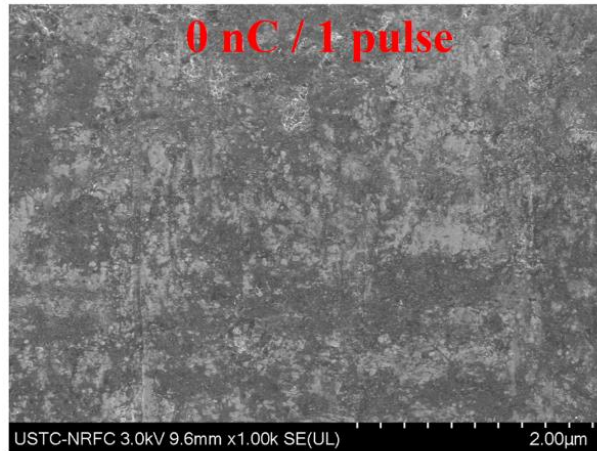


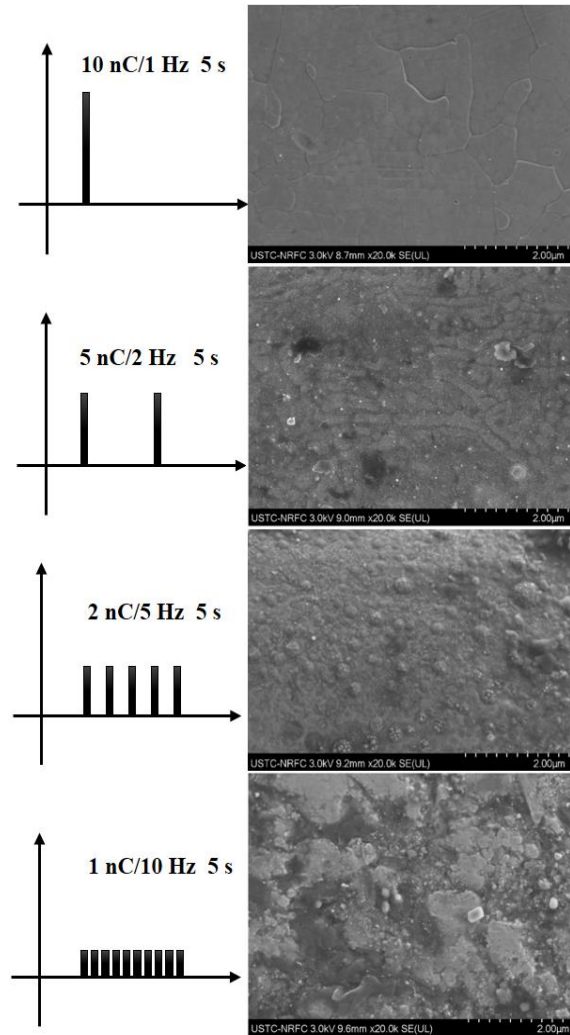
The experimental results of thermal conductivity with different crystallographic orientations



# Positron source for STCF

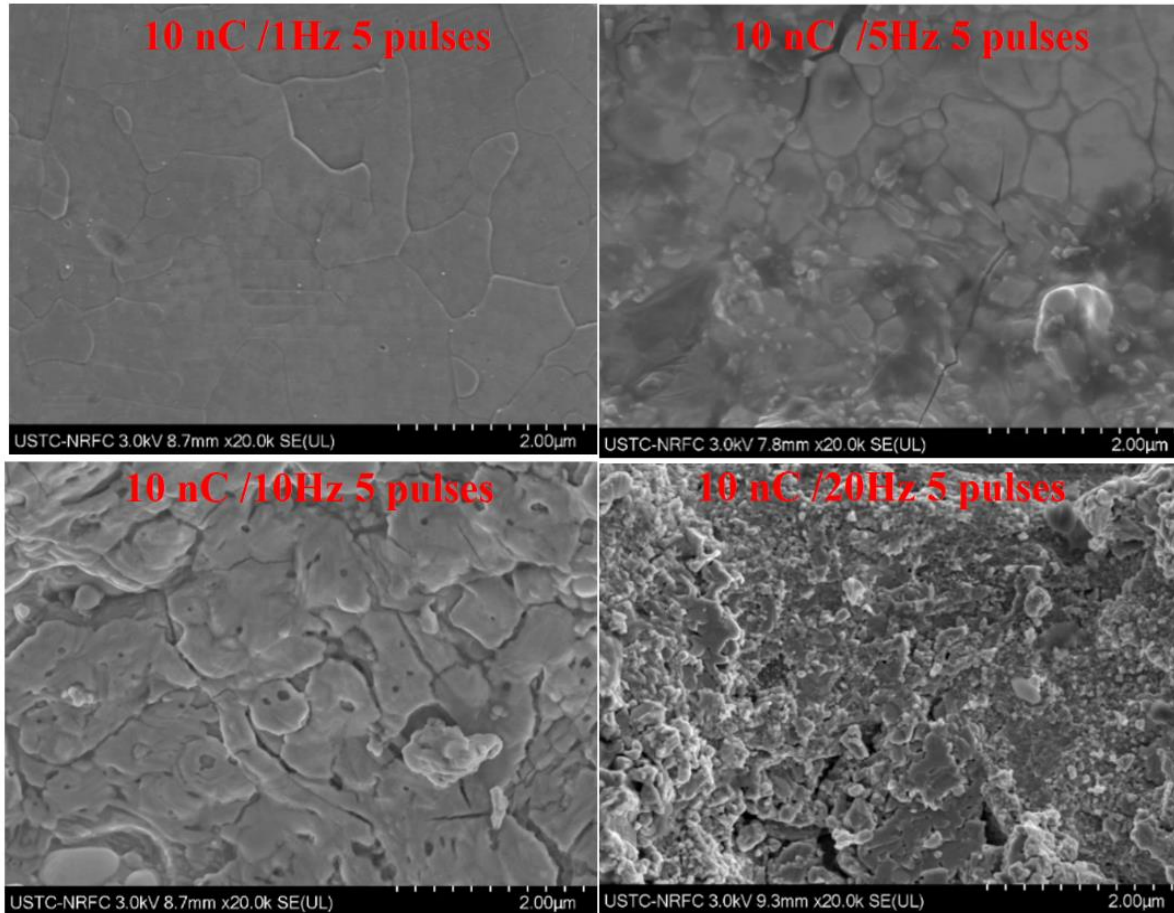
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A pulsed electron beam with different pulse structures but the same power was used to bombard the crystal tungsten target to study what conditions recrystallization occurred. Fig. 9 shows the results of 4 kinds of pulse structures. All structures had the same bombardment time of 5 seconds. It can be seen from the SEM results that there was obvious recrystallization at a time structure of  $10 \text{ nC}/1 \text{ Hz}$ , slight recrystallization at  $5 \text{ nC}/2 \text{ Hz}$ , and no recrystallization at  $2 \text{ nC}/5 \text{ Hz}$  and  $1 \text{ nC}/10 \text{ Hz}$ . This series of experiments shows that the main factor of recrystallization is not the average power of the bombardment electron beam but the relatively strong instantaneous power.









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**Table III Thermal conductivity changes in thermal conductivity after different electron beam bombardment**

Electron beam	Thermal conductivity (relatively)
0	1
10 nC single pulse	1.18
10 nC/1 Hz 5 s	1.12
10 nC/5 Hz 5 s	1.24
10 nC/10 Hz 5 s	2.02
10 nC/20 Hz 5 s	4.12



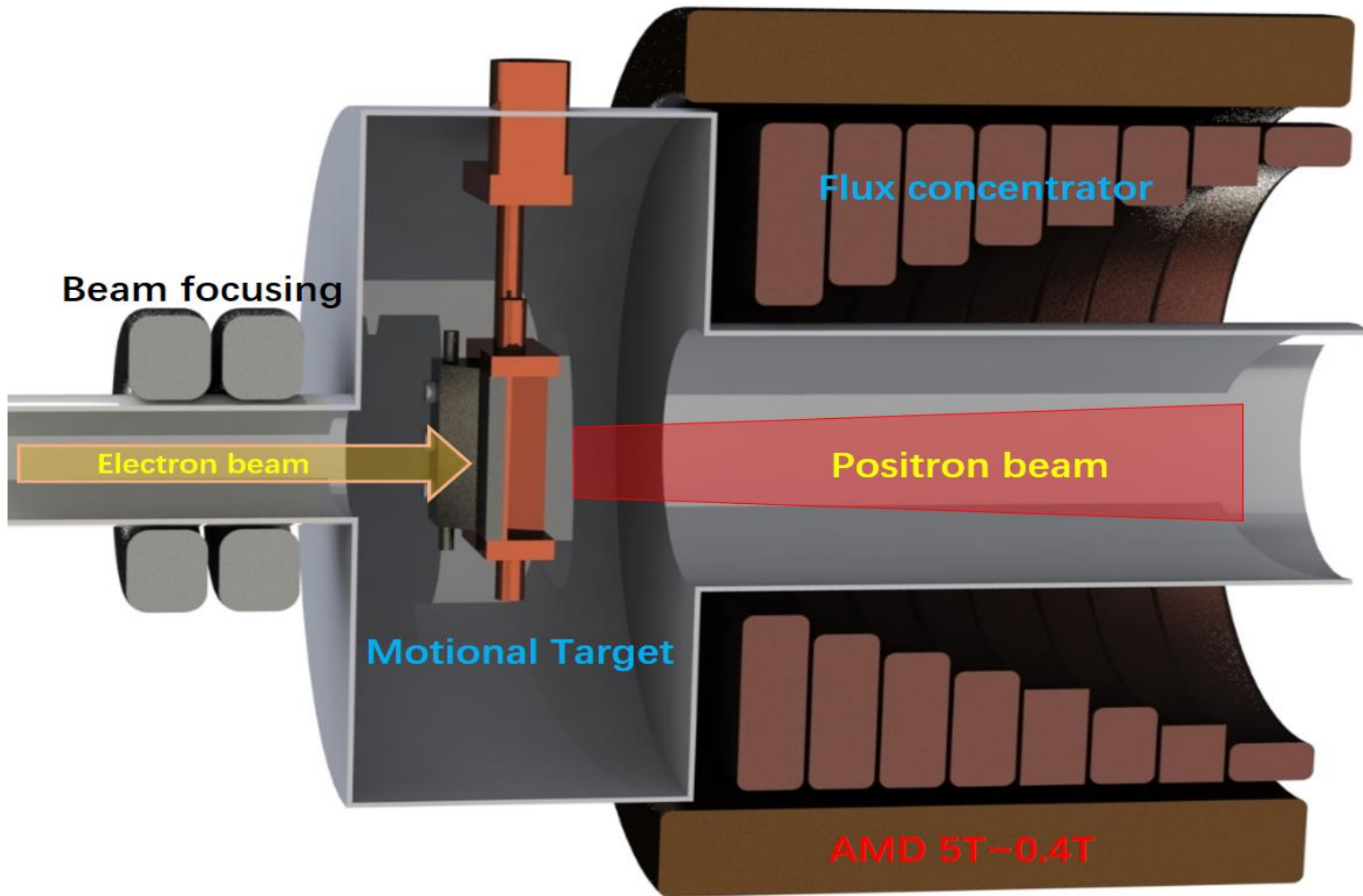
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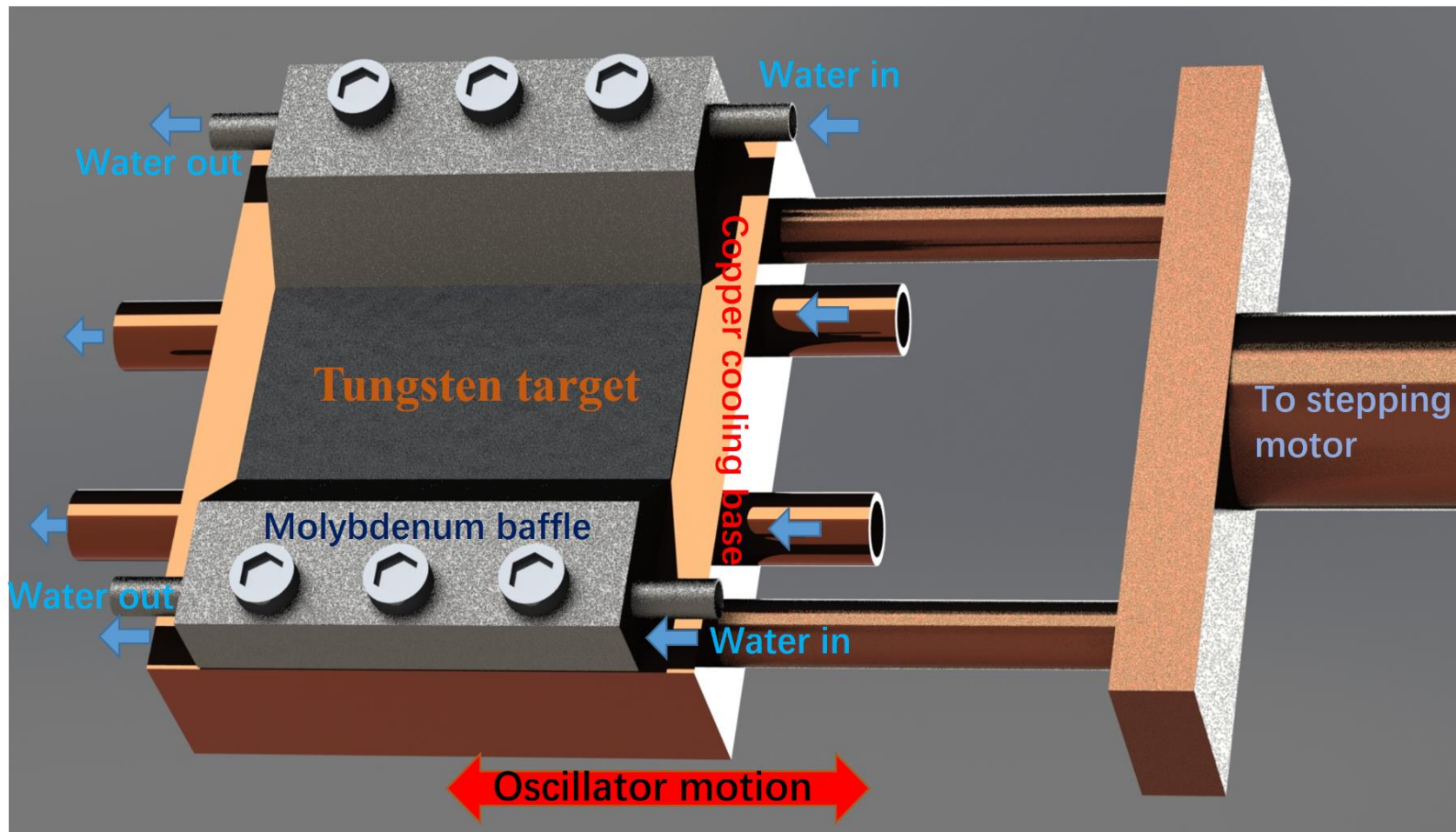
# The positron production system

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# The motional target for positron production

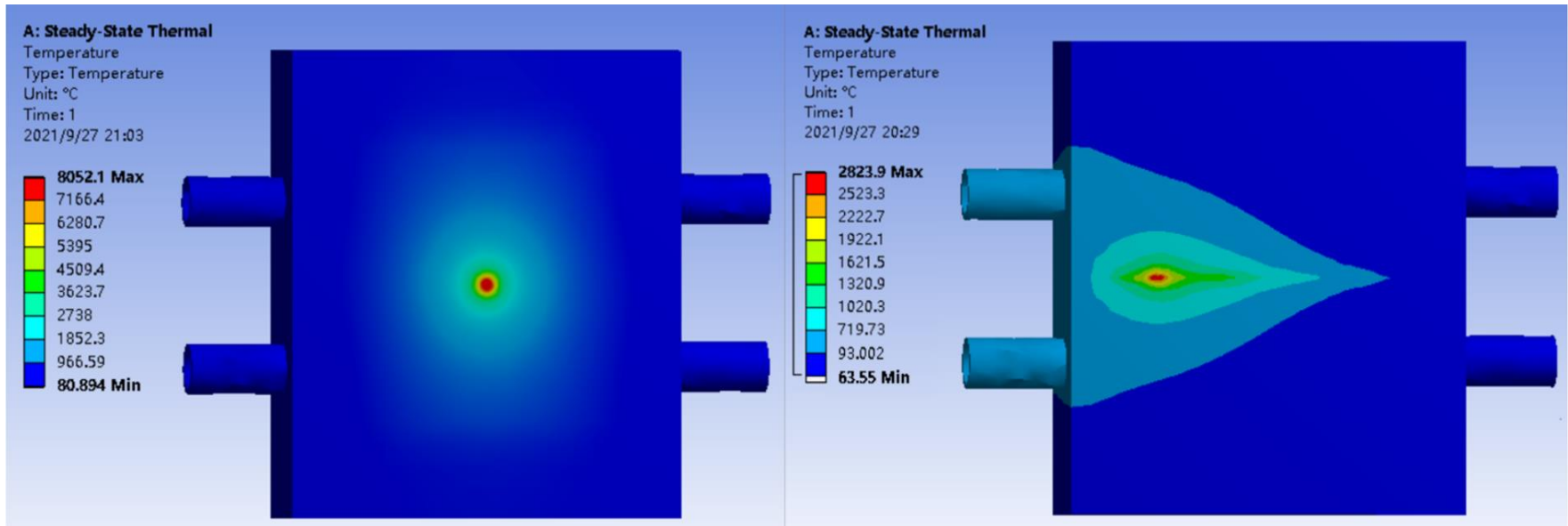
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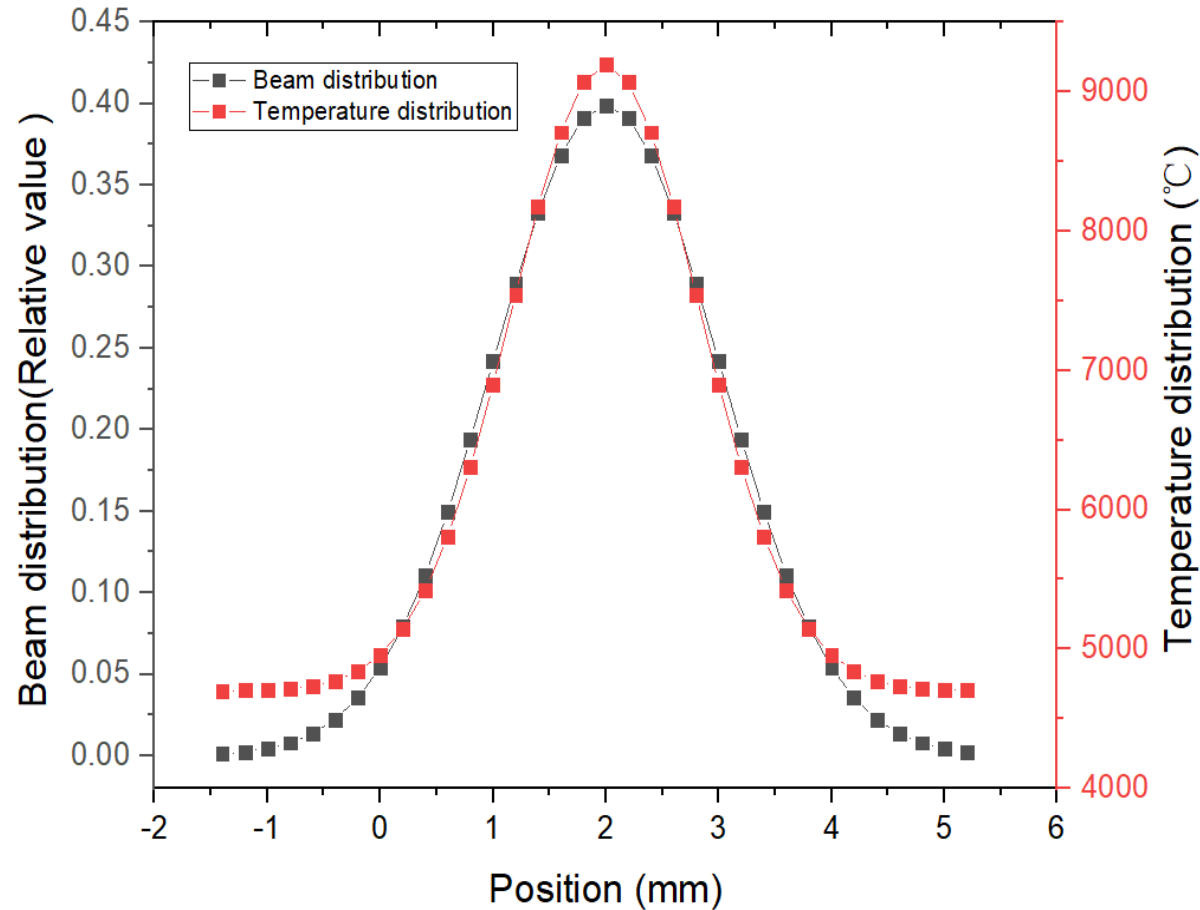


# Thermal simulation for motional target

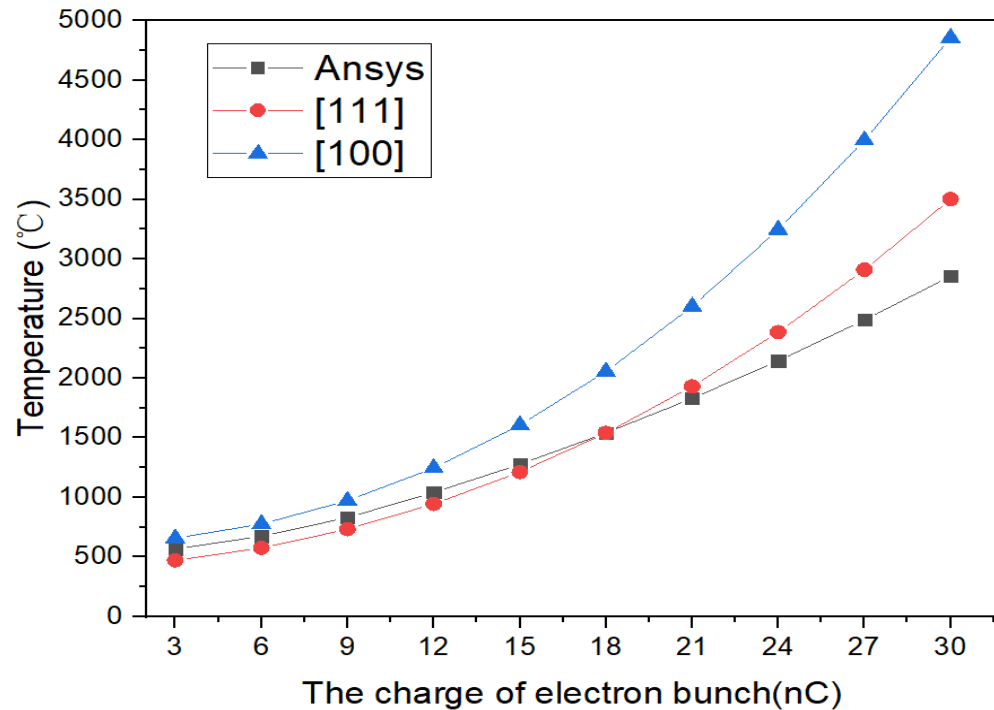
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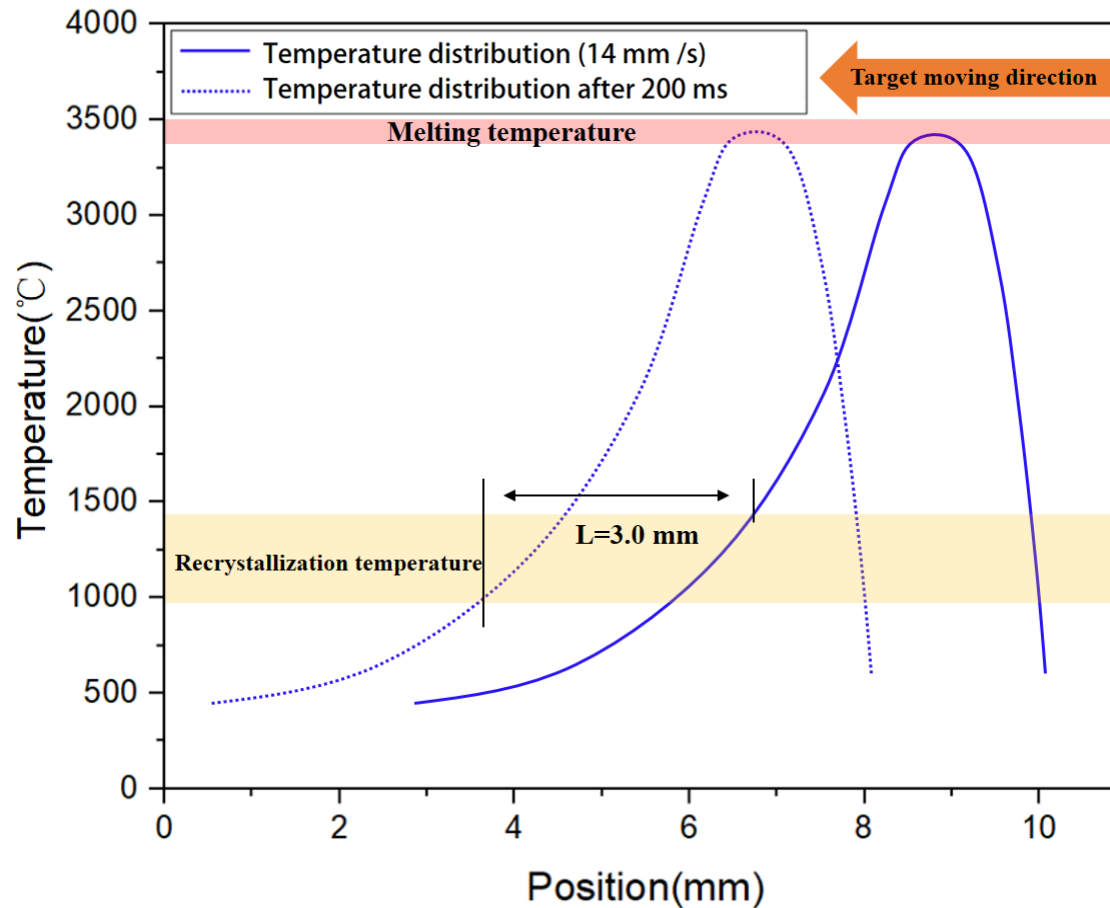
Simulation results of the static target (left) with strong water cooling and the motional target (right) with the same water cooling



The electron beam distribution and temperature distribution when the target is stationary (30 nC/100 Hz 1.5 GeV)



The difference between thermal simulation results considering and not considering the influence of the crystallographic orientation on thermal conductivity of various electron bunch charge. The repetition frequency is fixed at 100 Hz, electron energy is fixed at 1.5 GeV. Positive triangle - the thermal conductivity comes from the molecular dynamics simulation of [100] crystallographic orientation. Round - the thermal conductivity comes from the molecular dynamics simulation of [111] crystallographic orientation. Square - the thermal conductivity comes from the Ansys database for tungsten.



The temperature distribution when the target moves with the target speed of 14 mm/s (30 nC/100 Hz 1.5 GeV, 14 mm/s is melting point velocity)

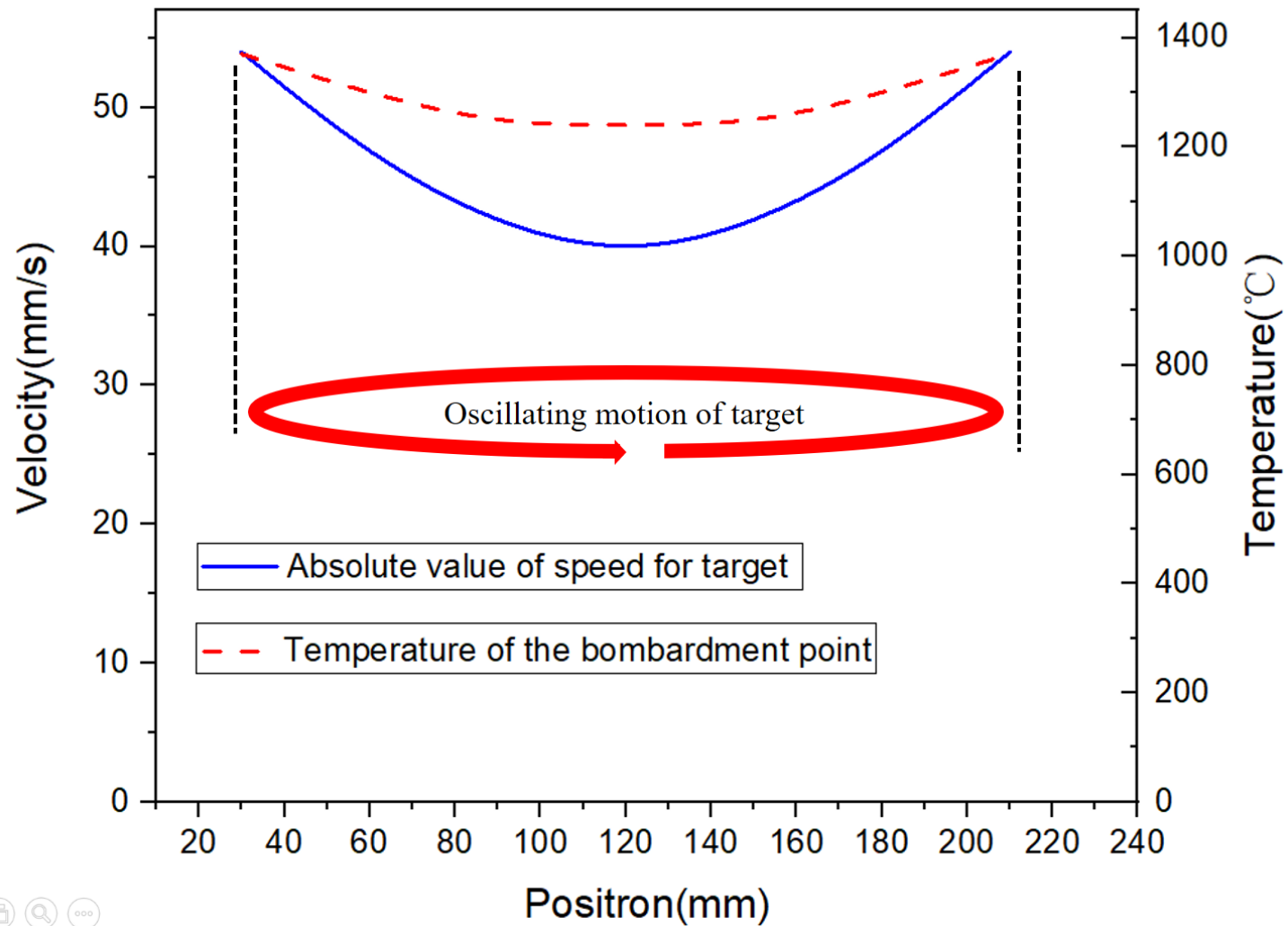




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Speed of the target (mm/s)	Temperature (°C)	Thermal effect
<14	>3401	Melting point exists
14-38	1400 -3401	Disordered recrystallization
38	1400	High recrystallization temperature
38-54	1231 -1400	Gentle recrystallization
54	1231	Minimum recrystallization time
54-177	900-1231	Incomplete recrystallization
>177	<900	Non-recrystallization



**Thanks for your attention !**